

In the Claims:

1. (Currently Amended) A method for manufacturing a MRAM, comprising the steps of:

forming a metal layer for a connection layer connected to a semiconductor substrate through a lower insulating layer;

sequentially forming a pinned magnetic layer, a tunnel barrier layer and a free magnetic layer on the metal layer;

forming a hard mask on the free magnetic layer;

etching the hard mask layer and the free magnetic layer in a ~~photolithography~~
photolithography process using a MTJ cell mask to expose the tunnel barrier layer;

sequentially forming a barrier layer and an insulating film on the entire surface;

anisotropically etching the insulating film to form an insulating film spacer on a sidewall of the hard mask layer and the free magnetic layer; and

etching the tunnel barrier layer, the pinned magnetic layer and the metal layer using the insulating film spacer and the hard mask layer as a mask to form a MTJ cell and a connection layer.